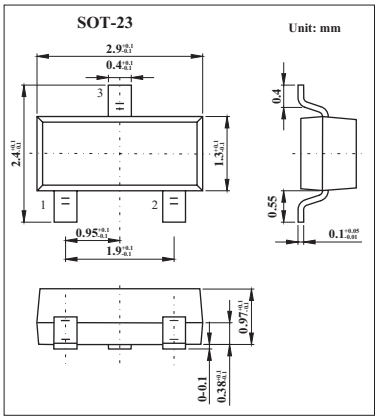
Silicon Schottky Barrier Diode

HSM107S



■ Features

- Low V_F and high efficiency.
- HSM107S which is interconnected in series configuration is designed for protection from not only external excessive voltage but also miss-operation on electric systems.
- MPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	8	V
Peak forward current	I_{FM}	0.1	A
Non-Repetitive Peak forward surge current	I_{FSM} (Note 1)	0.5	A
Average rectified current	I_O	50	mA
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

Note

1. Square wave, 10ms

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	V_R	V_R =1.0 mA	8			pF
Reverse current	I_R	V_R = 5 V			30	μA
Forward voltage	V_F	I_F = 10 mA			0.3	V
ESD-Capability (Note 1)		C=200pF , Both forward and reverse direction 1 pulse.	100			V

Note

1. Failure criterion ; $I_R \geqslant 60$ μA at V_R =5 V

■ Marking

Marking	C5